Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1010D-3 (SOT1215) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Trench MOSFET technology
- Leadless ultra small and thin SMD plastic package: 1.1 × 1.0 × 0.37 mm
- · Exposed drain pad for excellent thermal conduction
- ElectroStatic Discharge (ESD) protection 1 kV
- Very low Drain-Source on-state resistance R_{DSon} = 44 m Ω

3. Applications

- Low-side load switch and charging switch for portable devices
- · Power management in battery-driven portables
- · LED driver
- · DC-to-DC converters

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|-------------------|----------------------------------|--|-----|-----|-----|-----|------|
| V_{DS} | drain-source voltage | T _j = 25 °C | | - | - | 30 | V |
| V_{GS} | gate-source voltage | | | -20 | - | 20 | V |
| I _D | drain current | V _{GS} = 10 V; T _{amb} = 25 °C | [1] | - | - | 3.2 | Α |
| Static characte | Static characteristics | | | | | | |
| R _{DSon} | drain-source on-state resistance | V_{GS} = 10 V; I_D = 3.2 A; T_j = 25 °C | | - | 44 | 67 | mΩ |

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².



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5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------|---|----------------|
| 1 | G | gate | | D |
| 2 | S | source | | |
| 3 | D | drain | 4 3 | G ← ↓ □ 本 \ |
| 4 | D | drain | 2 | T N |
| | | | Transparent top view DFN1010D-3 (SOT1215) | S 017aaa255 |

6. Ordering information

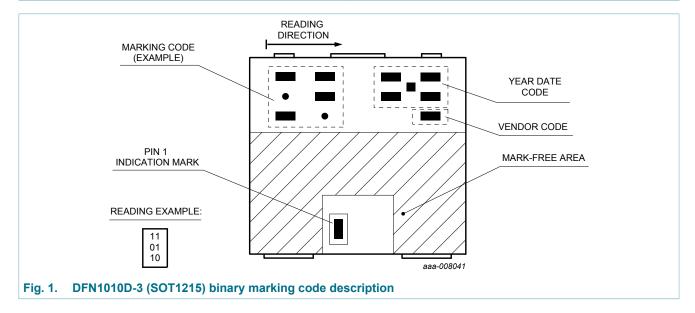
Table 3. Ordering information

| Type number | Package | | | | | |
|-------------|------------|--|---------|--|--|--|
| | Name | Description | Version | | | |
| PMXB65ENE | DFN1010D-3 | DFN1010D-3: plastic thermal enhanced ultra thin small outline package; no leads; 3 terminals; body 1.1 x 1.0 x 0.37 mm | SOT1215 | | | |

7. Marking

Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| PMXB65ENE | 00 10 00 |



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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|------------------|-------------------------|---|-----|-----|------|------|
| V_{DS} | drain-source voltage | T _j = 25 °C | | - | 30 | V |
| V_{GS} | gate-source voltage | | | -20 | 20 | V |
| I _D | drain current | V _{GS} = 10 V; T _{amb} = 25 °C | [1] | - | 3.2 | Α |
| | | V _{GS} = 10 V; T _{amb} = 100 °C | [1] | - | 2.5 | Α |
| I _{DM} | peak drain current | T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$ | | - | 12.8 | Α |
| P _{tot} | total power dissipation | T _{amb} = 25 °C | [2] | - | 0.4 | W |
| | | | [1] | - | 1.07 | W |
| | | T _{sp} = 25 °C | | - | 8.33 | W |
| Tj | junction temperature | | | -55 | 150 | °C |
| T _{amb} | ambient temperature | | | -55 | 150 | °C |
| T _{stg} | storage temperature | | | -65 | 150 | °C |
| Source-drain | n diode | | | | | |
| I _S | source current | T _{amb} = 25 °C | [1] | - | 0.9 | Α |

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

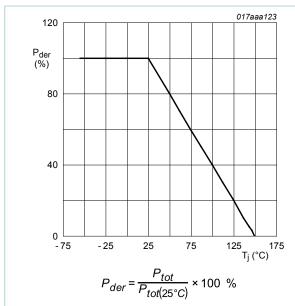


Fig. 2. Normalized total power dissipation as a function of junction temperature

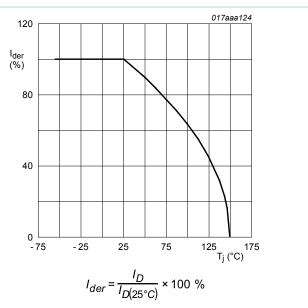


Fig. 3. Normalized continuous drain current as a function of junction temperature

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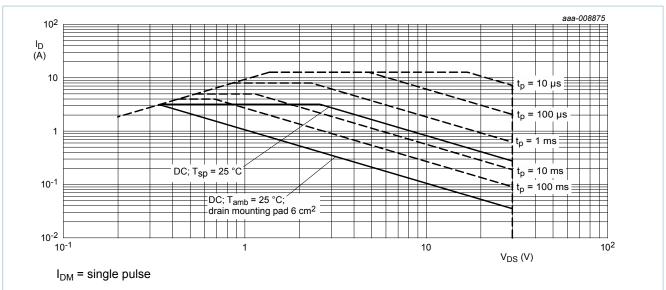


Fig. 4. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

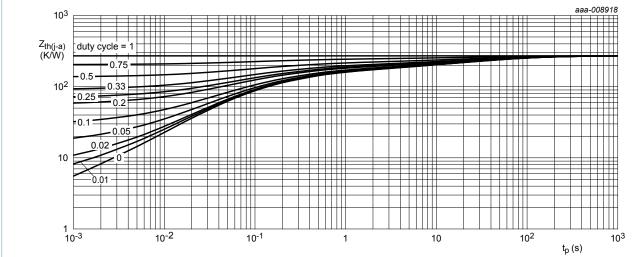
30 V, N-channel Trench MOSFET

9. Thermal characteristics

Table 6. Thermal characteristics

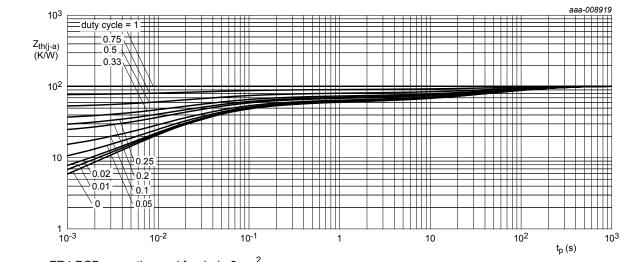
| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|-----------------------|---|---------------|-----|-----|-----|-----|------|
| R _{th(j-a)} | thermal resistance from junction to ambient | III II ee ali | [1] | - | 271 | 312 | K/W |
| | | | [2] | - | 102 | 117 | K/W |
| R _{th(j-sp)} | thermal resistance from junction to solder point | | | - | 10 | 15 | K/W |

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².



FR4 PCB, standard footprint

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 6 cm²

Fig. 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|----------------------|-----------------------------------|---|-----|-----|-----|------|
| Static chara | acteristics | | | ' | | , |
| V _{(BR)DSS} | drain-source breakdown voltage | I_D = 250 μ A; V_{GS} = 0 V; T_j = 25 °C | 30 | - | - | V |
| V_{GSth} | gate-source threshold voltage | I_D = 250 μ A; V_{DS} = V_{GS} ; T_j = 25 °C | 1 | 1.4 | 2 | V |
| I _{DSS} | drain leakage current | V _{DS} = 30 V; V _{GS} = 0 V; T _j = 25 °C | - | - | 1 | μA |
| I _{GSS} | gate leakage current | V _{GS} = 16 V; V _{DS} = 0 V; T _j = 25 °C | - | - | 10 | μA |
| | | V _{GS} = -16 V; V _{DS} = 0 V; T _j = 25 °C | - | - | -10 | μA |
| | | V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C | - | - | 1 | μA |
| | | V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C | - | - | -1 | μA |
| Doon | drain-source on-state | V_{GS} = 10 V; I_D = 3.2 A; T_j = 25 °C | - | 44 | 67 | mΩ |
| | resistance | V _{GS} = 10 V; I _D = 3.2 A; T _j = 150 °C | - | 71 | 107 | mΩ |
| | | V _{GS} = 4.5 V; I _D = 2.9 A | - | 56 | 79 | mΩ |
| 9 _{fs} | forward transconductance | V_{DS} = 10 V; I_D = 3.2 A; T_j = 25 °C | - | 26 | - | S |
| R _G | gate resistance | f = 1 MHz | - | 1 | - | Ω |
| Dynamic ch | naracteristics | | | ' | | , |
| Q _{G(tot)} | total gate charge | V _{DS} = 15 V; I _D = 3.2 A; V _{GS} = 10 V; | - | 6 | 11 | nC |
| Q _{GS} | gate-source charge | T _j = 25 °C | - | 0.7 | - | nC |
| Q _{GD} | gate-drain charge | | - | 0.9 | - | nC |
| C _{iss} | input capacitance | V _{DS} = 15 V; f = 1 MHz; V _{GS} = 0 V; | - | 295 | - | pF |
| C _{oss} | output capacitance | T _j = 25 °C | - | 40 | - | pF |
| C _{rss} | reverse transfer capacitance | | - | 31 | - | pF |
| t _{d(on)} | turn-on delay time | V_{DS} = 15 V; I_{D} = 3.2 A; V_{GS} = 10 V; | - | 3 | - | ns |
| t _r | rise time | $R_{G(ext)} = 6 \Omega; T_j = 25 ^{\circ}C$ | - | 12 | - | ns |
| t _{d(off)} | turn-off delay time | _ | - | 11 | - | ns |
| t _f | fall time | _ | - | 3 | - | ns |
| Source-drai | in diode | | 1 | | | , |
| V_{SD} | source-drain voltage | I _S = 0.9 A; V _{GS} = 0 V; T _i = 25 °C | - | 0.8 | 1.2 | V |

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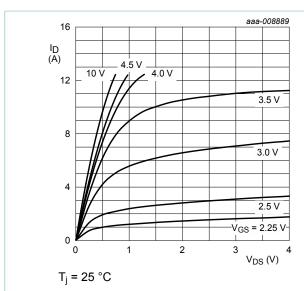


Fig. 7. Output characteristics: drain current as a function of drain-source voltage; typical values

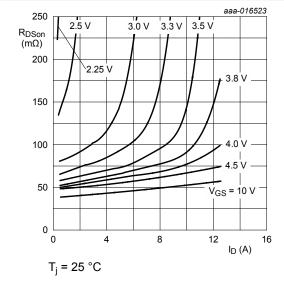


Fig. 9. Drain-source on-state resistance as a function of drain current; typical values

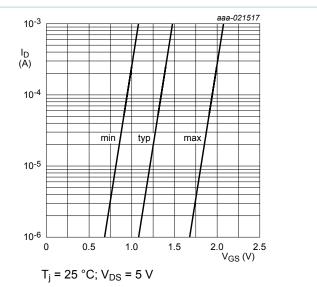


Fig. 8. Sub-threshold drain current as a function of gate-source voltage

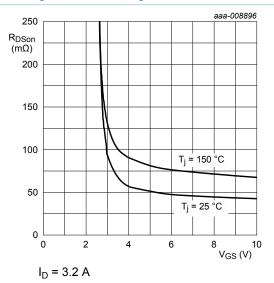


Fig. 10. Drain-source on-state resistance as a function of gate-source voltage; typical values

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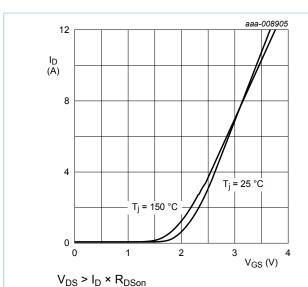


Fig. 11. Transfer characteristics: drain current as a function of gate-source voltage; typical values

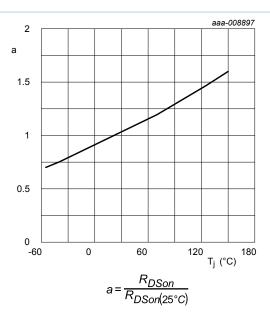


Fig. 12. Normalized drain-source on-state resistance as a function of junction temperature; typical values

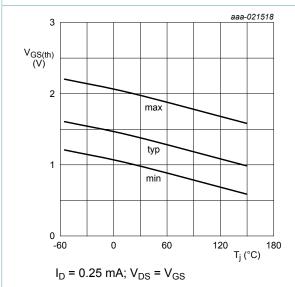
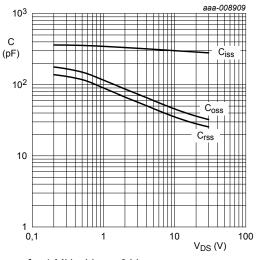


Fig. 13. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$

Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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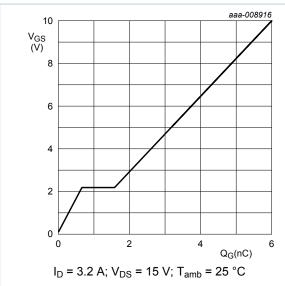


Fig. 15. Gate-source voltage as a function of gate charge; typical values

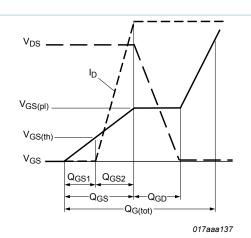


Fig. 16. MOSFET transistor: Gate charge waveform definitions

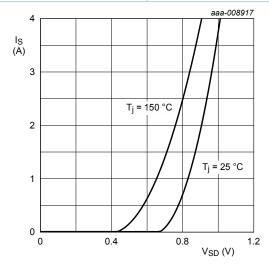
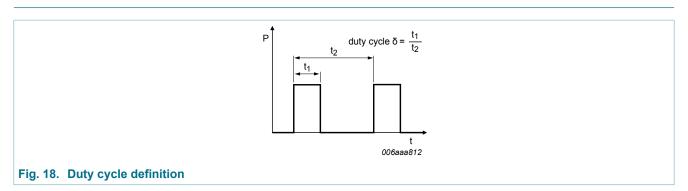


Fig. 17. Source current as a function of source-drain voltage; typical values

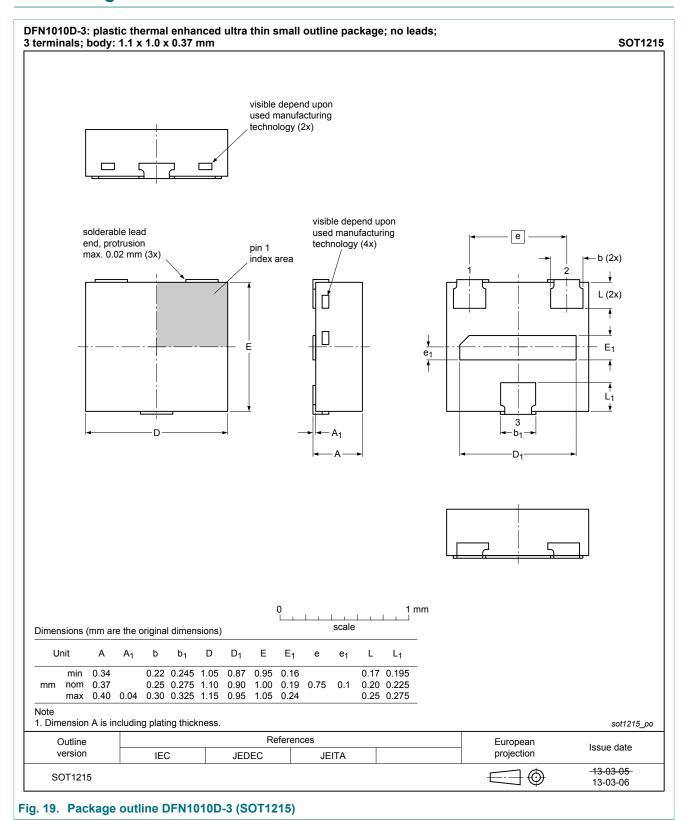
11. Test information

 $V_{GS} = 0 V$



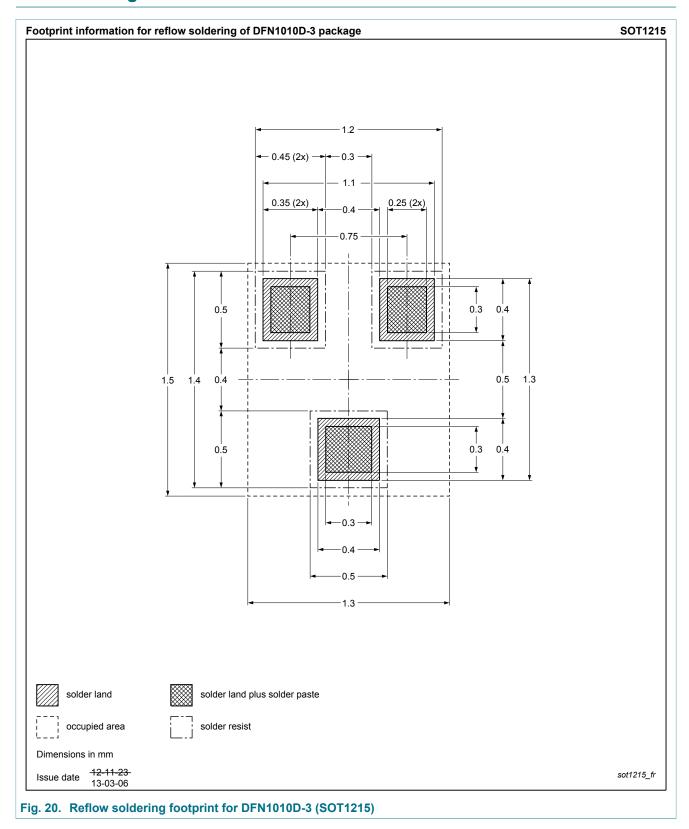
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12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

| | | · | | | | | | |
|----------------|--------------------|--|---------------|---------------|--|--|--|--|
| Data sheet ID | Release date | Data sheet status | Change notice | Supersedes | | | | |
| PMXB65ENE v.4 | 20161103 | Product data sheet | - | PMXB65ENE v.3 | | | | |
| Modifications: | Maximum value of g | Maximum value of gate-source threshold voltage revised | | | | | | |
| PMXB65ENE v.3 | 20150520 | Product data sheet | - | PMXB65ENE v.2 | | | | |
| PMXB65ENE v.2 | 20130924 | Product data sheet | - | PMXB65ENE v.1 | | | | |
| PMXB65ENE v.1 | 20130910 | Product data sheet | - | - | | | | |

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15. Legal information

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|--------------------------------------|--------------------|---|
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